

IN THE ABSTRACT:

Please amend the abstract as follows:

--ABSTRACT

A method of fabricating an exposure mask ~~for semiconductor manufacture to~~
~~improve the accuracy of critical dimensions of the mask pattern. The method includes~~ including the
steps of forming a chrome layer, a first photo resist, an Ag layer as a conductive layer and a second
photo resist on a transparent quartz substrate, in sequence; forming and using a second photo resist
pattern ~~by exposing and developing the second photo resist; forming to form~~ a conductive layer
pattern by etching the conductive layer ~~using the second photo resist pattern as an etch barrier;~~
removing the second photo resist pattern; forming an oxide layer ~~as a layer~~ for shielding light at the
surface of the conductive layer pattern and ~~by oxidizing the conductive layer pattern;~~ exposing the
first photo resist using the conductive layer pattern with having the oxide layer thereon ~~at the~~
~~surface thereof;~~ forming a first photo resist pattern exposing the chrome layer and ~~by developing the~~
~~exposed first photo resist;~~ forming a mask pattern including the chrome layer by selectively etching
the exposed chrome layer ~~parts;~~ and removing the conductive layer pattern including the oxide layer
and the first photo resist pattern.--